New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

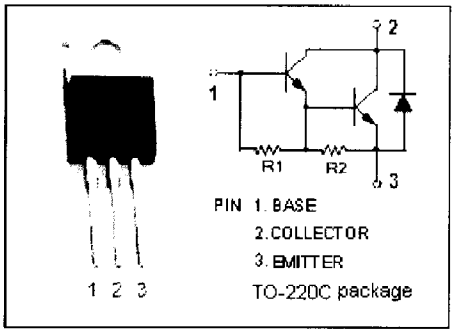
Silicon NPN Darlington Power Transistor — BDT63/A/B/C

DESCRIPTION

- Collector Current $-I_C$= 10A
- High DC Current Gain-h_{FE}= 1000(Min)@ I_C= 3A
- Complement to Type BDT62/A/B/C

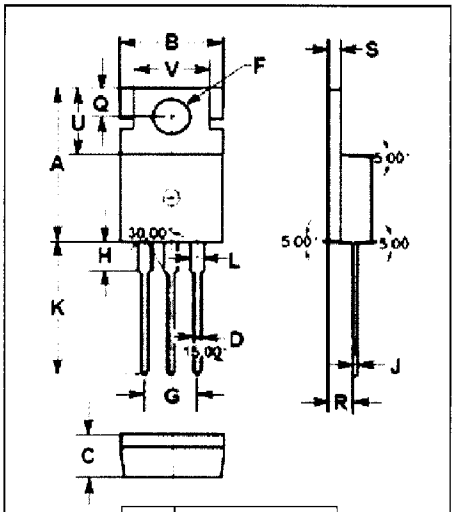
APPLICATIONS

- Designed for audio output stages and general purpose amplifier applications



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CER}	Collector-Emitter Voltage	BDT63	60	V
		BDT63A	80	
		BDT63B	100	
		BDT63C	120	
V_{CEO}	Collector-Emitter Voltage	BDT63	60	V
		BDT63A	80	
		BDT63B	100	
		BDT63C	120	
V_{EBO}	Emitter-Base Voltage		5	V
I_C	Collector Current-Continuous		10	A
I_{CM}	Collector Current-Peak		15	A
I_B	Base Current-Continuous		0.25	A
P_C	Collector Power Dissipation @ T_C=25℃		90	W
T_J	Junction Temperature		150	℃
T_{stg}	Storage Temperature Range		-65~150	℃



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.39	℃/W

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	BDT63	I_C= 30mA ; I_B=0	60			V
		BDT63A		80			
		BDT63B		100			
		BDT63C		120			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		I_C= 3A; I_B= 12mA			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		I_C= 8A; I_B= 80mA			2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage		I_C= 3A ; V_{CE}= 3V			2.5	V
V_{ECF}	C-E Diode Forward Voltage		I_F= 3A			2.0	V
I_{CEO}	Collector Cutoff Current		V_{CE}= $^1/_2V_{CEOmax}$; I_B= 0			0.5	mA
I_{CBO}	Collector Cutoff Current		V_{CB}= V_{CBOmax};I_E= 0 V_{CB}= $^1/_2V_{CBOmax}$;I_E= 0;T_C= 150℃			0.2 2.0	mA
I_{EBO}	Emitter Cutoff Current		V_{EB}= 5V; I_C=0			5	mA
h_{FE-1}	DC Current Gain		I_C= 3A ; V_{CE}= 3V	1000			
h_{FE-2}	DC Current Gain		I_C= 10A ; V_{CE}= 3V		3000		
C_{OB}	Output Capacitance		I_E= 0 ; V_{CB}= 10V; f_{test}= 1MHz		100		pF

Switching times

t_{on}	Turn-On Time	I_C= 3A; I_{B1}= -I_{B2}= 12mA; V_{CC}= 10V		1.0	2.5	μs
t_{off}	Turn-Off Time			5.0	10	μs